

Silicon NPN Power Transistors

KTC3229

DESCRIPTION

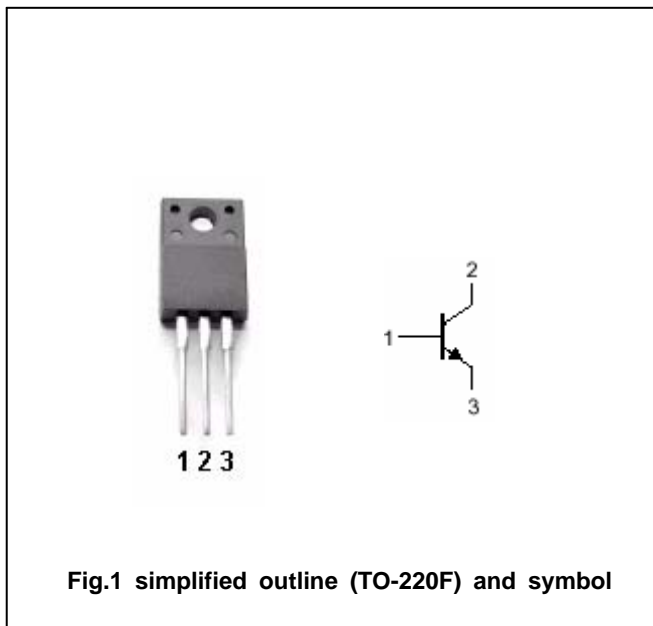
- With TO-220F package
- High voltage : $V_{CEO}=300V$

APPLICATIONS

- For color TV chroma output application

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings($T_a=25$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	300	V
V_{CEO}	Collector-emitter voltage	Open base	300	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		0.1	A
I_B	Base current		20	mA
P_C	Collector dissipation	$T_a=25$	2	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEsat}	Collector-emitter saturation voltage	I _C =10mA; I _B =1mA			1.0	V
I _{CBO}	Collector cut-off current	V _{CB} =240V; I _E =0			1.0	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			1.0	μA
h _{FE-1}	DC current gain	I _C =0.5mA; V _{CE} =10V	20			
h _{FE-2}	DC current gain	I _C =20mA; V _{CE} =10V	30		200	
f _T	Transition frequency	I _C =20mA; V _{CE} =20V	75			MHz
C _{OB}	Collector output capacitance	f=1MHz; V _{CB} =20V			4.0	pF

固电半导体

INCHANGE SEMICONDUCTOR

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PACKAGE OUTLINE

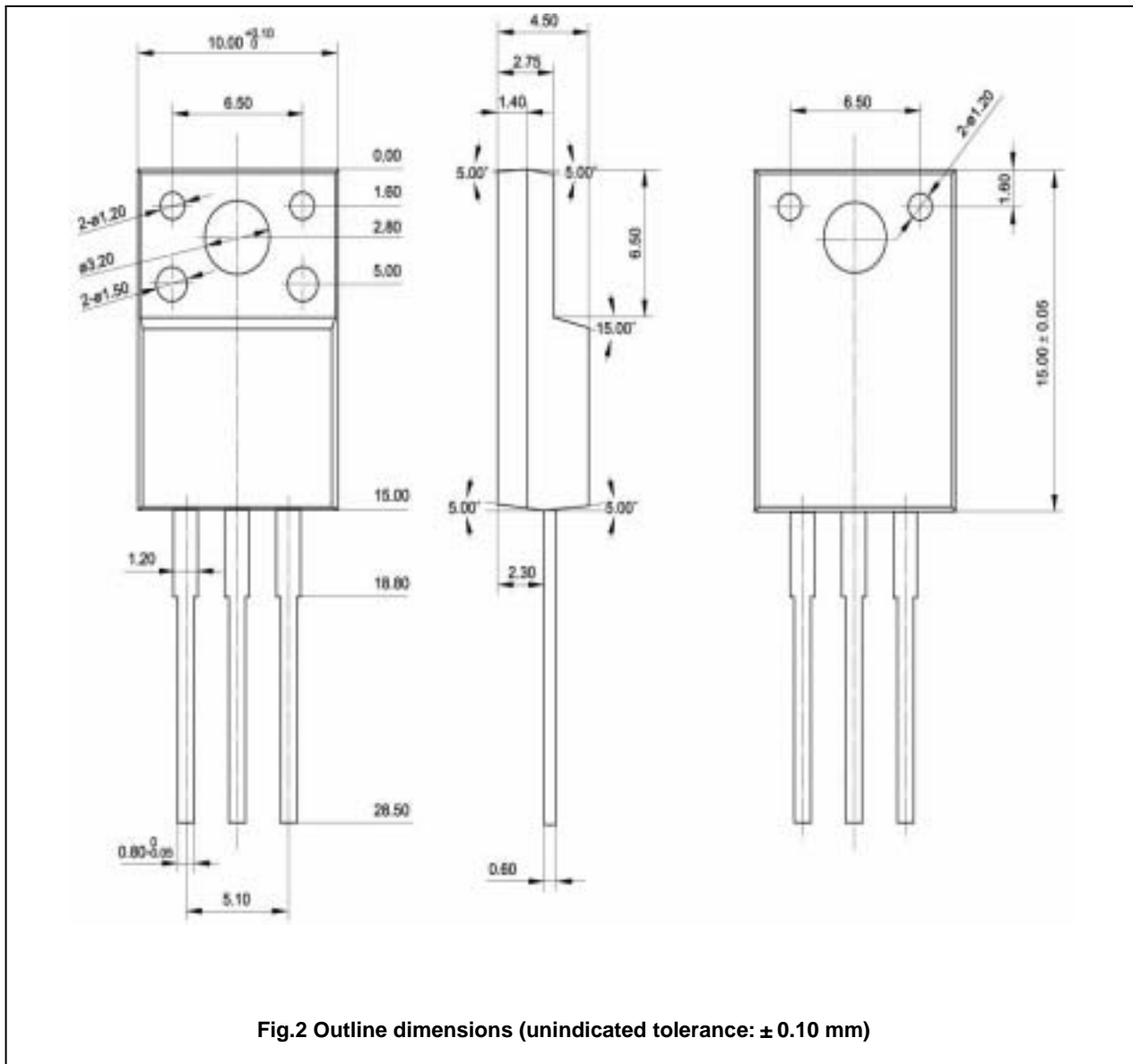


Fig.2 Outline dimensions (unindicated tolerance: ± 0.10 mm)

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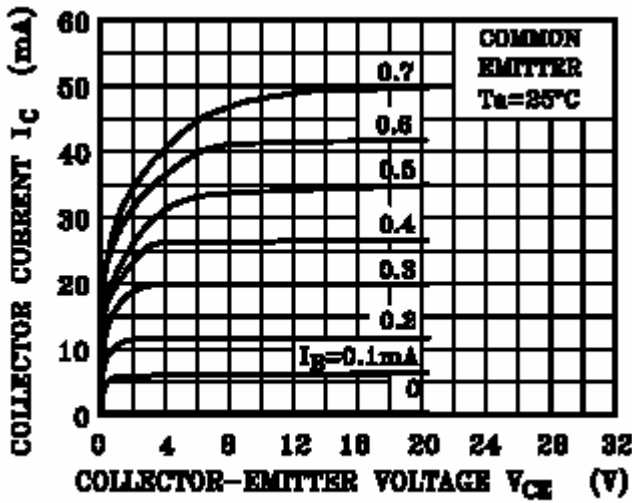


Fig.3 Static Characteristic

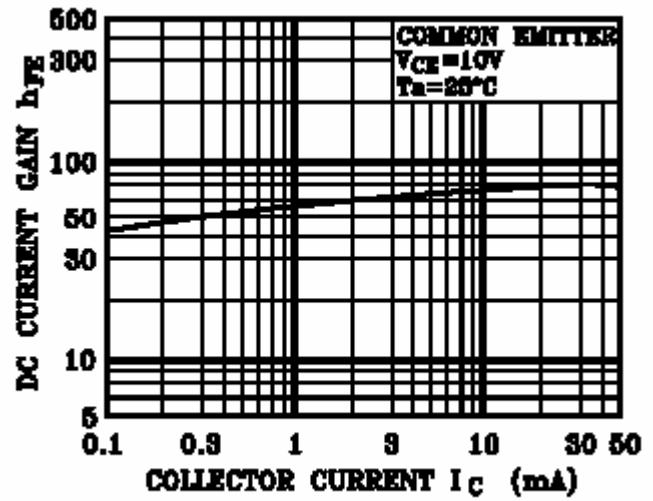


Fig.4 DC current Gain

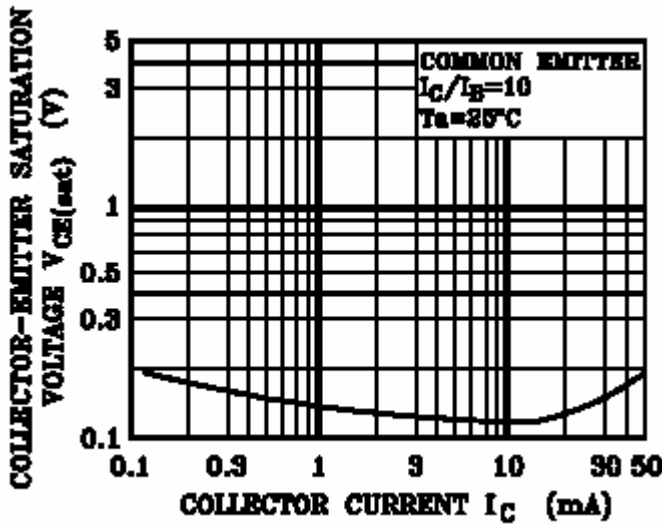


Fig.5 Collector-Emitter Saturation Voltage

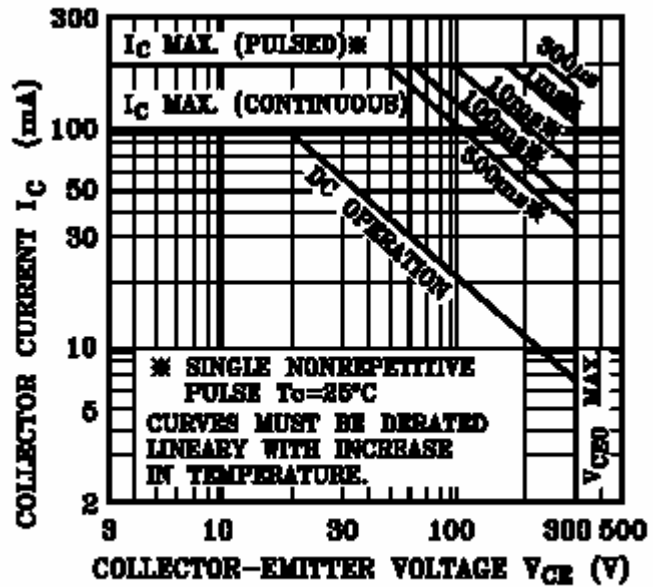


Fig.6 Safe Operating Area